

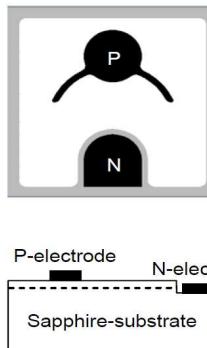
**Data Sheet**

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**LED Chip blue**
**EOLC-460-34**

Rev. 02, 2017

Radiation	Type	Electrodes
Blue	InGaN / sapphire	N+P-up

	Chip size: 13 mil x 13 mil (330 ± 25 µm x 330 ± 25 µm) Thickness: 3.5 mil (90 ± 10 µm) N, P bonding pads: Ø3.5 mil (Ø90 ± 25 µm), Au alloy 100% probing test Passivation layer on top
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**Absolute Maximum Ratings**
 $T_{amb}$ = 25°C, unless otherwise specified

Parameter	Symbol	Rating	Unit
Forward DC current	I <sub>F</sub>	30	mA
Reverse voltage	I <sub>R</sub>	5	V
Junction temperature	T <sub>J</sub>	115	°C
Storage temperature chip	T <sub>STG</sub>	-40...+85	°C
Storage temperature chip on tape	T <sub>STG</sub>	+0...+40	°C
Transport. temperature chip on tape	T <sub>STG</sub>	-20...+65	°C
Soldering temperature	T <sub>SOL</sub>	+280 (10 sec)	°C

**Optical and Electrical Characteristics**
 $T_{amb}$ = 25°C, unless otherwise specified

Parameter	Symbol	Cond.	Min	Typ	Max	Unit
Forward voltage	V <sub>F</sub>	I <sub>F</sub> =10 µA	2.0			V
Forward voltage	V <sub>F</sub>	I <sub>F</sub> =20 mA	2.8		3.6	V
Reverse current	I <sub>R</sub>	V <sub>R</sub> =5 V			2	µA
Radiant power*	I <sub>V</sub>	I <sub>F</sub> =20 mA	125	150		mcd
Dominant wavelength	λ <sub>D</sub>	I <sub>F</sub> =20 mA	455	460	465	nm
FWHM	Δλ <sub>0.5</sub>	I <sub>F</sub> =20 mA		25		nm

\*Measured on bare chip on TO-18 header

**Packing**

Dice on adhesive film with wire-bond on top



We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.